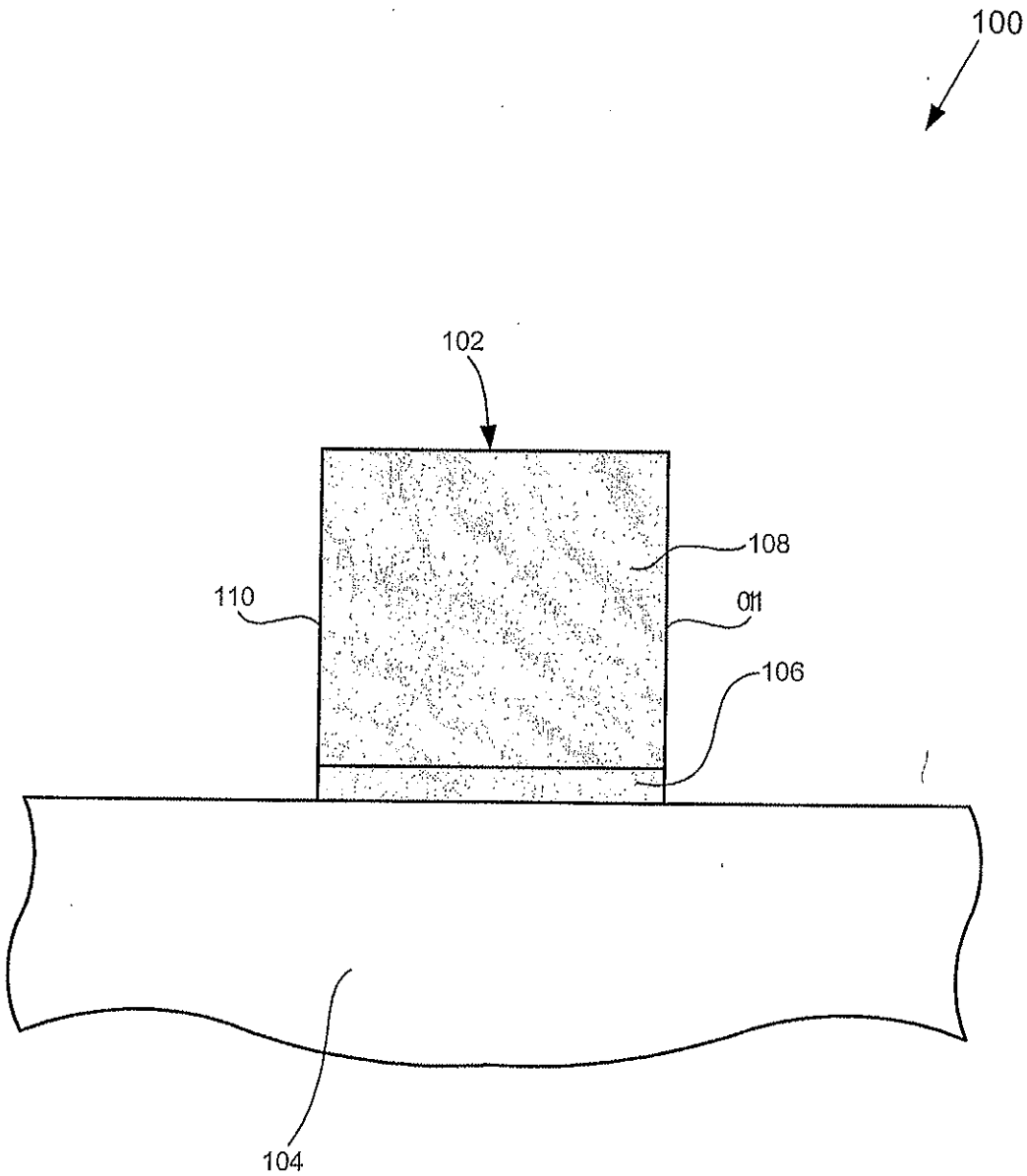

100
102
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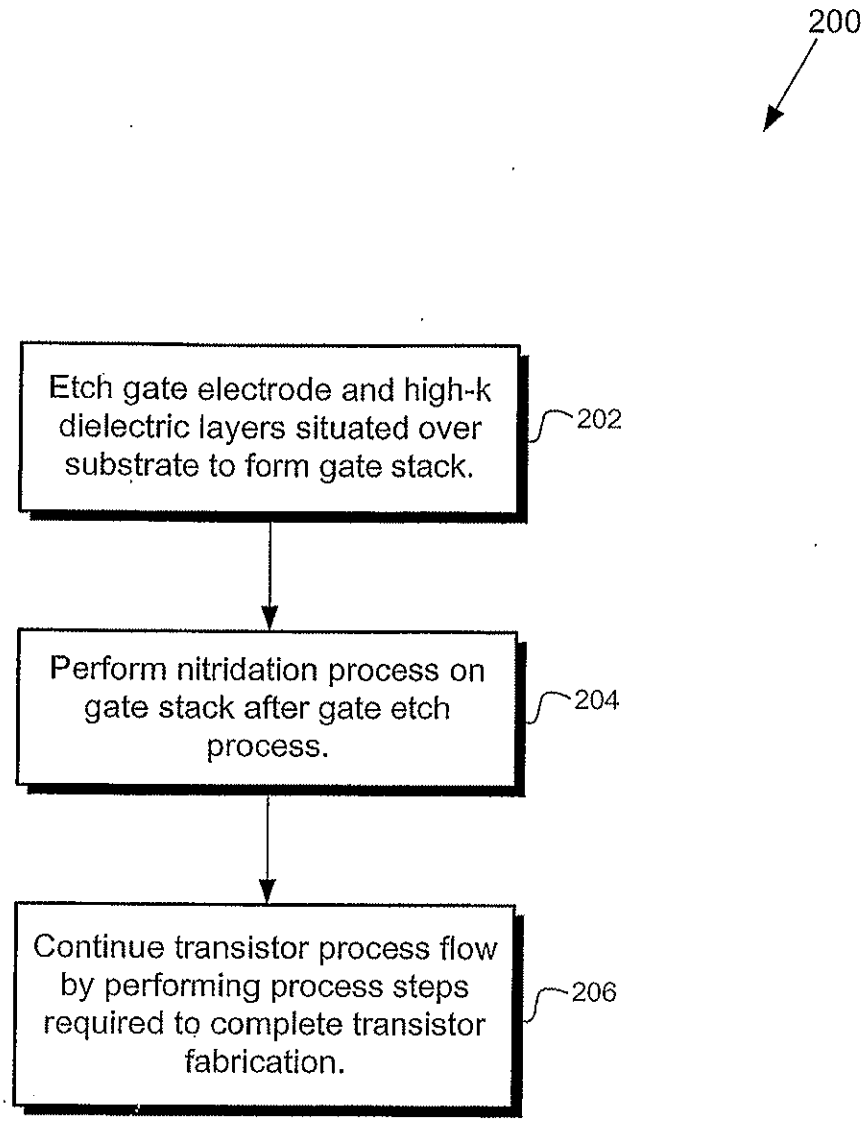

200
Etch gate electrode and high-k dielectric layers situated over substrate to form gate stack.
202
Perform nitridation process on gate stack after gate etch process.
204
Continue transistor process flow by performing process steps required to complete transistor fabrication.
206

Fig. 2